Digital Transistors (BRT) R1 = 2.2 k Ω , R2 = ∞ k Ω

PNP Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25° C)

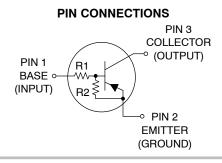
Rating	Symbol	Max	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Collector Current – Continuous	Ι _C	100	mAdc
Input Forward Voltage	V _{IN(fwd)}	12	Vdc
Input Reverse Voltage	V _{IN(rev)}	5	Vdc

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

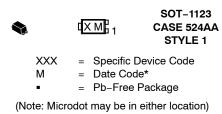


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MARKING DIAGRAM



*Date Code orientation may vary depending upon manufacturing location.

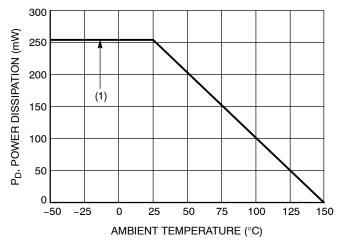
ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

Table 1. ORDERING INFORMATION

Device	Part Marking	Package	Shipping [†]
NSBA123TF3T5G	F (90°)*	SOT-1123	8,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. * $(xx^{\circ}) =$ Degree rotation in the clockwise direction.



(1) SOT-1123; 100 mm², 1 oz. copper trace

Figure	1.	Derating	Curve
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Table 2. THERMAL CHARACTERISTICS

Characteristic		Symbol	Max	Unit
THERMAL CHARACTERISTICS (SOT-1123) (NSBA123TF3)				
Total Device Dissipation T _A = 25°C Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P _D	254 297 2.0 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	493 421	°C/W
Thermal Resistance, Junction to Lead	(Note 1)	$R_{\theta JL}$	193	°C/W
Junction and Storage Temperature Range		T _J , T _{stg}	–55 to +150	°C

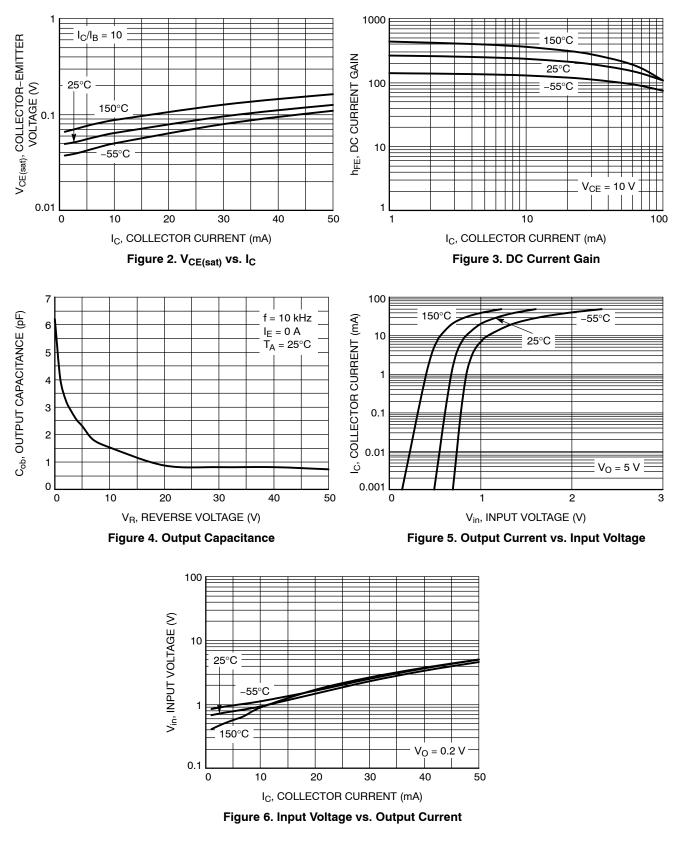
1. FR-4 @ 100 mm², 1 oz. copper traces, still air. 2. FR-4 @ 500 mm², 1 oz. copper traces, still air.

Table 3. ELECTRICAL CHARACTERISTICS (T_A = 25° C, unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector-Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_E = 0)$	I _{CBO}	-	-	100	nAdc
Collector–Emitter Cutoff Current $(V_{CE} = 50 \text{ V}, I_B = 0)$	I _{CEO}	_	_	500	nAdc
Emitter-Base Cutoff Current ($V_{EB} = 6.0 \text{ V}, I_C = 0$)	I _{EBO}	_	_	4.0	mAdc
Collector-Base Breakdown Voltage $(I_C = 10 \ \mu A, I_E = 0)$	V _(BR) CBO	50	_	-	Vdc
Collector–Emitter Breakdown Voltage (Note 3) $(I_{C} = 2.0 \text{ mA}, I_{B} = 0)$	V _{(BR)CEO}	50	_	-	Vdc
ON CHARACTERISTICS					
DC Current Gain (Note 3) (I _C = 5.0 mA, V _{CE} = 10 V)	h _{FE}	160	350	-	
Collector–Emitter Saturation Voltage (Note 3) $(I_C = 10 \text{ mA}, I_B = 0.3 \text{ mA})$	V _{CE(sat)}	_	_	0.25	Vdc
Input Voltage (off) (V _{CE} = 5.0 V, I _C = 100 μA)	V _{i(off)}	-	0.6	-	Vdc
Input Voltage (on) ($V_{CE} = 0.2 \text{ V}, I_C = 10 \text{ mA}$)	V _{i(on)}	_	0.9	-	Vdc
Output Voltage (on) (V _{CC} = 5.0 V, V _B = 2.5 V, R _L = 1.0 k Ω)	V _{OL}	_	_	0.2	Vdc
Output Voltage (off) ($V_{CC} = 5.0 \text{ V}, \text{ V}_{B} = 0.5 \text{ V}, \text{ R}_{L} = 1.0 \text{ k}\Omega$)	V _{OH}	4.9	_	-	Vdc
Input Resistor	R1	1.5	2.2	2.9	kΩ
Resistor Ratio	R ₁ /R ₂	_	-	-	

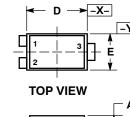
3. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle $\leq 2\%.$

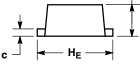




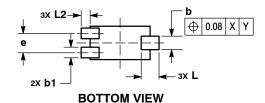
PACKAGE DIMENSIONS

SOT-1123 CASE 524AA ISSUE C









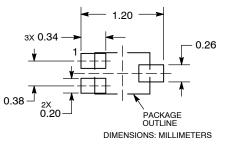
NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- MINIMUM THICKNESS OF BASE MATERIAL. 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.34	0.40	
b	0.15	0.28	
b1	0.10	0.20	
С	0.07	0.17	
D	0.75	0.85	
Е	0.55	0.65	
е	0.35	0.40	
HE	0.95	1.05	
L	0.185	REF	
L2	0.05	0.15	
STYL			

2. EMITTER 3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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